

DRD5460Y20

Rectifier Diode

DS6231-1 February 2018 (LN35176)

Replaces DS4171-6.0 February 2003 – Datasheet DS2102SY-DS2102SV

FEATURES

- Double Side Cooling
- High Surge Capability

KEY PARAMETERS

| V_{RRM} | 2000V |
|--------------------|-------|
| I _{F(AV)} | 6654A |
| I _{FSM} | 100kA |

VOLTAGE RATINGS

| Part and Ordering Number | Repetitive Peak Voltages V _{RRM} V | Conditions |
|--|--|----------------------------|
| DRD5460Y20 DRD5460Y18 DRD5460Y16 | 2000 1800 1600 | $V_{RSM} = V_{RRM} + 100V$ |

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DRD5460Y18 for a 1800V device

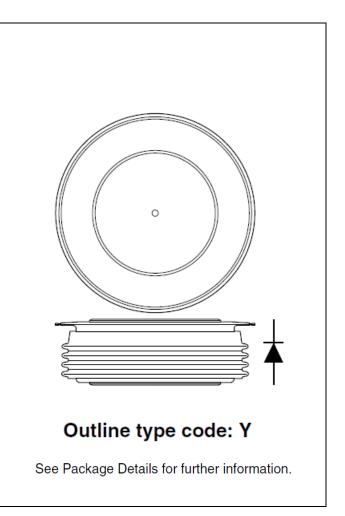


Fig. 1 Package outline



CURRENT RATINGS

T_{case} = 75°C unless stated otherwise

| Symbol | Parameter | Test Conditions | Max. | Units | | |
|---------------------------------|--------------------------------------|--------------------------|-------|-------|--|--|
| Double Si | Double Side Cooled | | | | | |
| I _{F(AV)} | Mean forward current | Half wave resistive load | 6654 | Α | | |
| I _{F(RMS)} | RMS value | - | 10452 | А | | |
| I _F | Continuous (direct) on-state current | - | 9275 | А | | |
| Single Side Cooled (Anode side) | | | | | | |
| I _{F(AV)} | Mean forward current | Half wave resistive load | 4227 | Α | | |
| I _{F(RMS)} | RMS value | - | 6640 | Α | | |
| I _F | Continuous (direct) on-state current | - | 5403 | А | | |

T_{case} = 100°C unless stated otherwise

| Symbol | Parameter | Test Conditions | Max. | Units | | |
|---------------------|--------------------------------------|--------------------------|------|-------|--|--|
| Double Si | Double Side Cooled | | | | | |
| $I_{F(AV)}$ | Mean forward current | Half wave resistive load | 5460 | А | | |
| I _{F(RMS)} | RMS value | - | 8575 | А | | |
| I _F | Continuous (direct) on-state current | - | 7450 | А | | |
| Single Sid | Single Side Cooled (Anode side) | | | | | |
| I _{F(AV)} | Mean forward current | Half wave resistive load | 3410 | А | | |
| I _{F(RMS)} | RMS value | - | 5356 | А | | |
| l _F | Continuous (direct) on-state current | - | 4620 | А | | |



SURGE RATINGS

| Symbol | Parameter | Test Conditions | Max. | Units |
|------------------|---|---|------|-------------------|
| I _{FSM} | Surge (non-repetitive) on-state current | 10ms half sine, T _{case} = 175°C | 80.0 | kA |
| l ² t | I ² t for fusing | $V_R = 50\% V_{RRM} - \frac{1}{4}$ sine | 32 | MA ² s |
| I _{FSM} | Surge (non-repetitive) on-state current | 10ms half sine, T _{case} = 175°C | 100 | kA |
| l ² t | I ² t for fusing | $V_R = 0$ | 50 | MA ² s |

THERMAL AND MECHANICAL RATINGS

| Symbol | Parameter | Test Conditions | | Min. | Max. | Units |
|----------------------|---------------------------------------|--------------------------|-------------|------|--------|-------|
| R _{th(j-c)} | Thermal resistance – junction to case | Double side cooled | DC | - | 0.0095 | °C/W |
| | | Single side cooled | Anode DC | - | 0.019 | °C/W |
| | | | Cathode DC | - | 0.019 | °C/W |
| R _{th(c-h)} | Thermal resistance – case to heatsink | Clamping force 43kN | Double side | - | 0.002 | °C/W |
| | | (with mounting compound) | Single side | - | 0.004 | °C/W |
| T_{vj} | Virtual junction temperature | On-state (conducting) | | - | 185 | °C |
| | | Reverse (blocking) | | - | 175 | °C |
| T _{stg} | Storage temperature range | | | -55 | 175 | °C |
| F _m | Clamping force | | | 38.0 | 47.0 | kN |

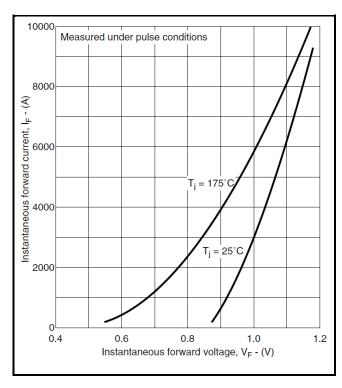
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CHARACTERISTICS

| Symbol | Parameter | Test Conditions | Min. | Max. | Units |
|-----------------|-------------------------------|---|------|--------|-------|
| V_{FM} | Forward voltage | At 3000A peak, T _{case} = 25°C | - | 1.0 | V |
| I _{RM} | Peak reverse current | At V _{RRM} , T _{case} = 175°C | - | 100 | mA |
| Qs | Total stored charge | I _F = 2000A, dI _{RR} /dt =3A/μs | - | 2600 | μC |
| Irr | Peak reverse recovery current | $T_{case} = 175^{\circ}C, V_{R} = 100V$ | - | 120 | Α |
| V _{TO} | Threshold voltage | At T _{vj} = 175°C | - | 0.75 | V |
| r _T | Slope resistance | At T _{vj} = 175°C | - | 0.0415 | mΩ |

CURVES



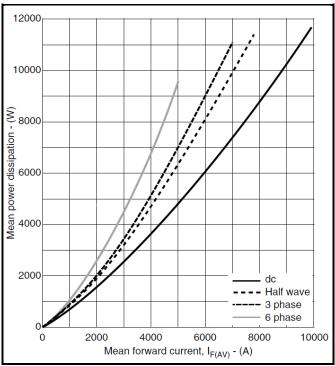


Fig.2 Maximum & minimum on-state characteristics

Fig.3 Dissipation curves

 V_{TM} EQUATION

 $V_{TM} = A + Bln (I_T) + C.I_T + D.\sqrt{I_T}$

Where A = 0.402091

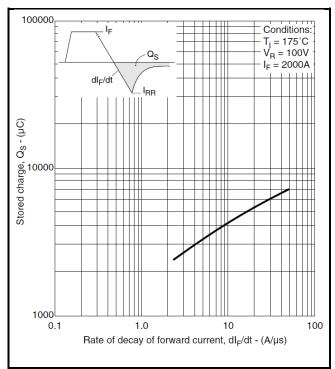
B = 0.011718

 $C = 6.48 \times 10^{-5}$

D = 0.005977

these values are valid for $T_j = 175$ °C for $I_F 500$ A to 10000A





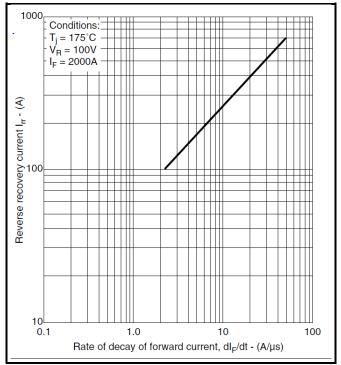
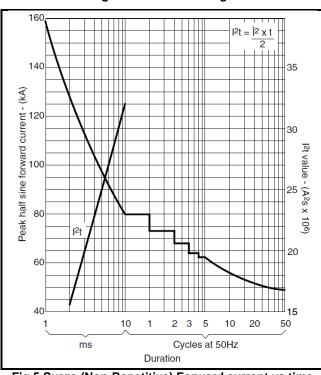
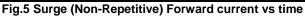


Fig.4 Total stored charge

Fig.5 Maximum reverse recovery current





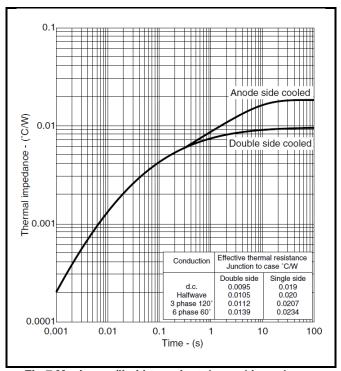


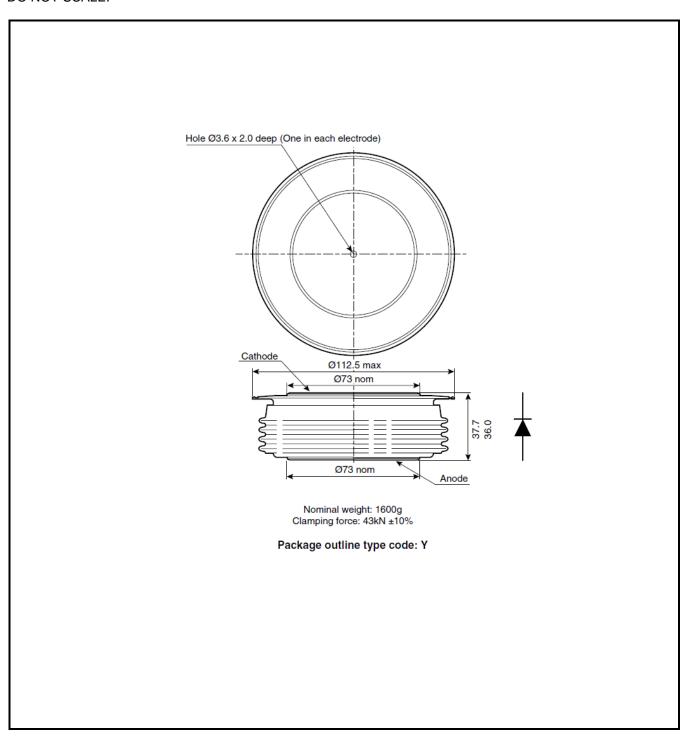
Fig.7 Maximum (limit) transient thermal impedancejunction to case

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PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



Note:

Some packages may be supplied with gate and or tags.



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